

BOE001 Electronic Devices

3L:0T:0P

3 credits

Module 1

Introduction to Semiconductor Physics: Review of Quantum Mechanics, Electrons in periodic Lattices, E-k diagrams. Energy bands in intrinsic and extrinsic silicon; Carrier transport: diffusion current, drift current, mobility and resistivity; sheet resistance, design of resistors

Module 2

Generation and recombination of carriers; Poisson and continuity equation P-N junction characteristics, I-V characteristics, and small signal switching models; Avalanche breakdown, Zener diode, Schottky diode

Module 3

Bipolar Junction Transistor, I-V characteristics, Ebers-Moll Model, MOS capacitor, C-V characteristics, MOSFET, I-V characteristics, and small signal models of MOS transistor, LED, photodiode and solar cell;

Module 4

Integrated circuit fabrication process: oxidation, diffusion, ion implantation, photolithography, etching, chemical vapor deposition, sputtering, twin-tub CMOS process.

Text /Reference Books:

1. G. Streetman, and S. K. Banerjee, "Solid State Electronic Devices," 7th edition, Pearson, 2014.
2. D. Neamen, D. Biswas "Semiconductor Physics and Devices," McGraw-Hill Education
3. S. M. Sze and K. N. Kwok, "Physics of Semiconductor Devices," 3rd edition, John Wiley & Sons, 2006.
4. C.T. Sah, "Fundamentals of solid state electronics," World Scientific Publishing Co. Inc, 1991.
5. Y. Tsividis and M. Colin, "Operation and Modeling of the MOS Transistor," Oxford Univ. Press, 2011.

Course Outcomes:

At the end of this course students will demonstrate the ability to

1. Understand the principles of semiconductor Physics
2. Understand and utilize the mathematical models of semiconductor junctions and MOS transistors for circuits and systems.


Registrar
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Dean

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Effective from session 2020-21


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